

isc Triacs

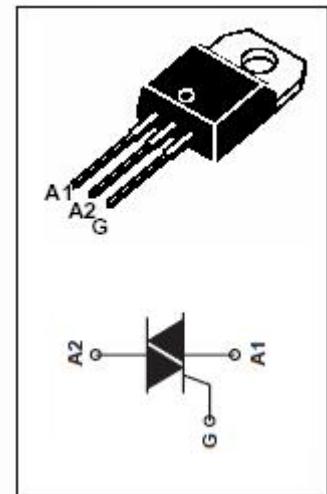
BTA08-600B

FEATURES

- With TO-220AB insulated package
- Suitable for general purpose applications where gate high sensitivity is required. Application on 4Q such as phase control and static switching.

ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	MIN	UNIT
V _{DRM}	Repetitive peak off-state voltage	600	V
V _{RRM}	Repetitive peak reverse voltage	600	V
I _{T(RMS)}	RMS on-state current (full sine wave) T _j =105°C	8	A
I _{TSM}	Non-repetitive peak on-state current t _p =20ms	80	A
T _j	Operating junction temperature	110	°C
T _{stg}	Storage temperature	-45~150	°C
R _{th(j-c)}	Thermal resistance, junction to case	4.3	°C/W
R _{th(j-a)}	Thermal resistance, junction to ambient	60	°C/W

ELECTRICAL CHARACTERISTICS (T_c=25°C unless otherwise specified)

SYMBOL	PARAMETER	CONDITIONS		MAX	UNIT
I _{RRM}	Repetitive peak reverse current	V _R =V _{RRM} , V _R =V _{RRM} , T _j =110°C		0.01 0.5	mA
I _{DRM}	Repetitive peak off-state current	V _D =V _{DRM} , V _D =V _{DRM} , T _j =110°C		0.01 0.5	mA
I _{GT}	Gate trigger current	I	V _D =12V; R _L = 33 Ω		50
		II			50
		III			50
		IV			100
I _H	Holding current	I _{GT} = 0.1A, Gate Open		50	mA
V _{GT}	Gate trigger voltage all quadrant	V _D =12V; R _L = 33 Ω		1.5	V
V _{TM}	On-state voltage	I _T = 11A; t _p = 380 μ s		1.75	V